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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
$V_{DS}(V)$ $R_{DS(on)}(\Omega)$ $I_{D}(A)$				
100	$0.095 \text{ at V}_{GS} = 10 \text{ V}$	15		
	0.100 at V _{GS} = 6 V	15		

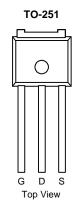
FEATURES

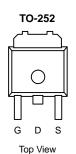
- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R_g Tested

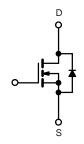


APPLICATIONS

· Primary Side Switch







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C =	= 25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	100			
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Proin Current /T 475 °C\b	T _C = 25 °C	I-	15		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	l _D	8.7		
Pulsed Drain Current		I _{DM}	45	А	
Continuous Source Current (Diode Conduction)	I _S	15			
Avalanche Current	I _{AR}	15			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	11.3	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	62 ^b	W	
iviaximum rower bissipation	T _A = 25 °C] 'D [2.7 ^a		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	16	20	°C/W	
Junction-to-Ambient*	Steady State		45	55		
Junction-to-Case		R _{thJC}	2	2.4		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



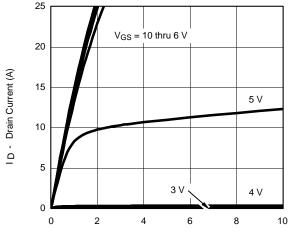
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l l		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 100 V, V _{GS} = 0 V	1		1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	μA	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	15			Α	
		V _{GS} = 10 V, I _D = 15 A		0.095	0.110	Ω	
5 : 0 . 0 b	D	V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.190		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.250		
		V _{GS} = 6 V, I _D = 10 A		0.100	0.115		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		25		S	
Dynamic ^a							
Input Capacitance	C _{iss}			900			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		115		pF	
Reverse Transfer Capacitance	C _{rss}			70			
Total Gate Charge ^c	Q_g			20	25		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		5.5		nC	
Gate-Drain Charge ^c	Q_{gd}			7			
Gate Resistance	R_g		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			8	12		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		35	55	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		17	17 25		
Fall Time ^c	t _f			30	45		
Source-Drain Diode Ratings and Char	racteristic (T	_C = 25 °C)					
Pulsed Current	I _{SM}				45	Α	
Diode Forward Voltage ^b	V _{SD}	I _F = 15 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 15 A, dl/dt = 100 A/μs		55	85	ns	

Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. Independent of operating temperature.

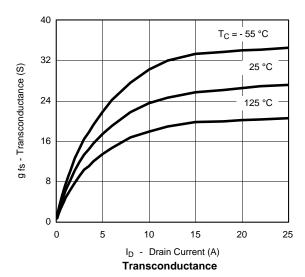
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

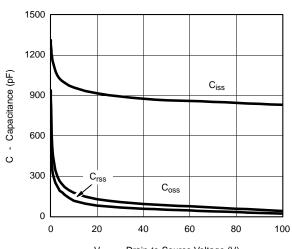
TYPICAL CHARACTERISTICS (25 °C unless noted)



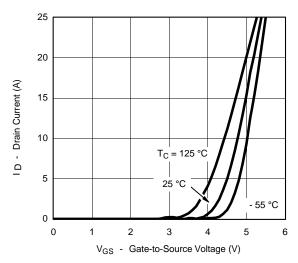
 $V_{DS}\,$ - Drain-to-Source Voltage (V)

Output Characteristics

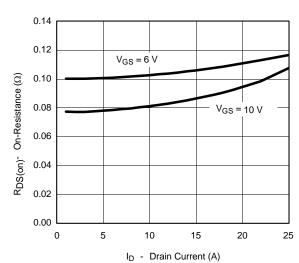




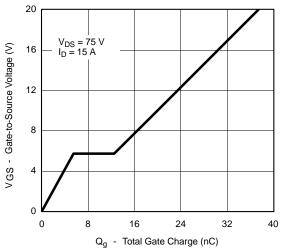
 $V_{DS}\,$ - Drain-to-Source Voltage (V) Capacitance



Transfer Characteristics



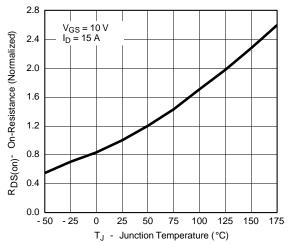
On-Resistance vs. Drain Current



Gate Charge

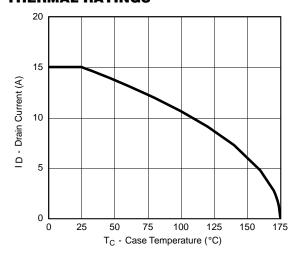
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TYPICAL CHARACTERISTICS (25 °C unless noted)

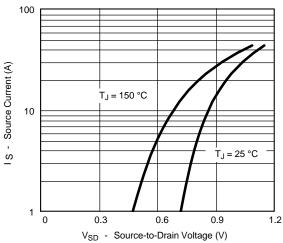


On-Resistance vs. Junction Temperature

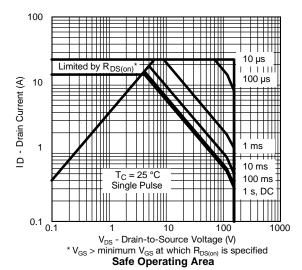
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage

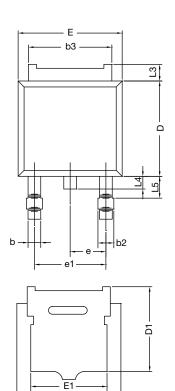


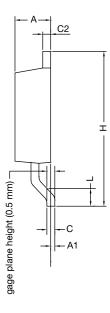
Normalized Thermal Transient Impedance, Junction-to-Case





TO-252AA CASE OUTLINE





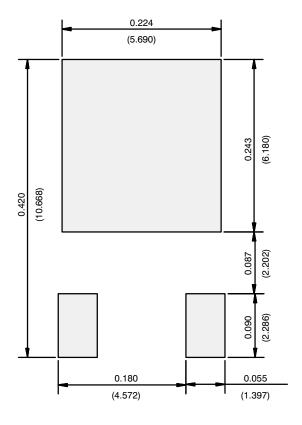
	MILLIN	METERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

DWG: 5347 Note

• Dimension L3 is for reference only.



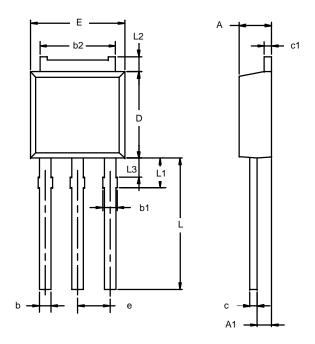
RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



TO-251AA (DPAK)



Note:	Dimension	L3 is for	reference only.
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	MILLIN	IETERS	INC	HES	
Dim	Min	Max	Min	Max	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
b	0.71	0.89	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.43	0.206	0.214	
С	0.46	0.58	0.018	0.023	
с1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
Е	6.48	6.73	0.255	0.265	
е	2.28	BSC	0.090 BSC		
L	8.89	9.53	0.350	0.375	
L1	1.91	2.28	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.045	0.060	
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346					

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